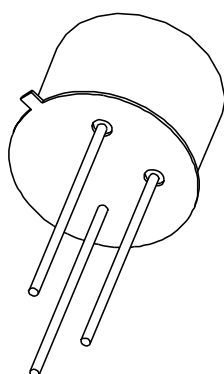


DATA SHEET



BSX62; BSX63 NPN switching transistors

Product specification
Supersedes data of September 1994
File under Discrete Semiconductors, SC04

1997 Jun 19

NPN switching transistors

BSX62; BSX63

FEATURES

- High current (max. 3 A)
- Low voltage (max. 60 V).

APPLICATIONS

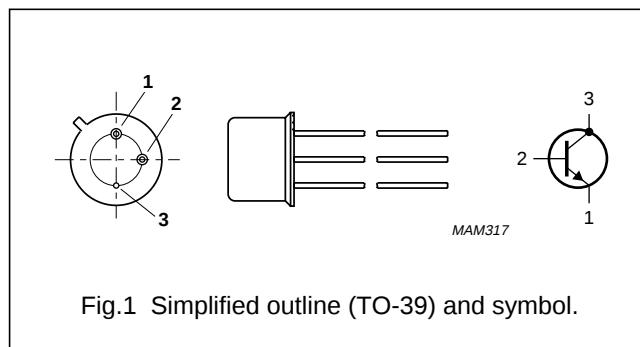
- Medium power switching.

DESCRIPTION

NPN switching transistor in a TO-39 metal package.

PINNING

PIN	DESCRIPTION
1	emitter
2	base
3	collector, connected to case



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{CBO}	collector-base voltage BSX62 BSX63	open emitter	— —	— —	60 80	V V
V_{CEO}	collector-emitter voltage BSX62 BSX63	open base	— —	— —	40 60	V V
I_C	collector current (DC)		—	—	3	A
P_{tot}	total power dissipation	$T_{case} \leq 25\text{ °C}$	—	—	5	W
h_{FE}	DC current gain BSX62-10; BSX63-10 BSX62-16; BSX63-16	$I_C = 1\text{ A}$; $V_{CE} = 1\text{ V}$	63 100	100 160	160 250	
f_T	transition frequency	$I_C = 200\text{ mA}$; $V_{CE} = 10\text{ V}$; $f = 100\text{ MHz}$	30	70	—	MHz
t_{off}	turn-off time	$I_{Con} = 1\text{ A}$; $I_{Bon} = 50\text{ mA}$; $I_{Boff} = -50\text{ mA}$	—	—	1.5	μs

NPN switching transistors

BSX62; BSX63

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter			
	BSX62		–	60	V
	BSX63		–	80	V
V_{CEO}	collector-emitter voltage	open base			
	BSX62		–	40	V
	BSX63		–	60	V
V_{EBO}	emitter-base voltage	open collector	–	5	V
I_C	collector current (DC)		–	3	A
I_{CM}	peak collector current		–	3	A
I_{BM}	peak base current		–	500	mA
P_{tot}	total power dissipation	$T_{case} \leq 25\text{ °C}$	–	5	W
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	200	°C
T_{amb}	operating ambient temperature		–65	+150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	in free air	200	K/W
$R_{th\ j-c}$	thermal resistance from junction to case		28	K/W

NPN switching transistors

BSX62; BSX63

CHARACTERISTICS

$T_{\text{case}} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current BSX62	$V_{\text{CB}} = 40\text{ V}$	–	–	100	nA
		$V_{\text{CB}} = 40\text{ V}; T_{\text{case}} = 150\text{ }^{\circ}\text{C}$	–	–	100	μA
I_{CBO}	collector cut-off current BSX63	$V_{\text{CB}} = 60\text{ V}$	–	–	100	nA
		$V_{\text{CB}} = 60\text{ V}; T_{\text{case}} = 150\text{ }^{\circ}\text{C}$	–	–	100	μA
I_{EBO}	emitter cut-off current	$I_{\text{C}} = 0; V_{\text{EB}} = 5\text{ V}$	–	–	100	nA
h_{FE}	DC current gain BSX62-10; BSX63-10 BSX62-16; BSX63-16	$I_{\text{C}} = 100\text{ mA}; V_{\text{CE}} = 1\text{ V}$	–	110	–	
			–	180	–	
h_{FE}	DC current gain BSX62-10; BSX63-10 BSX62-16; BSX63-16	$I_{\text{C}} = 1\text{ A}; V_{\text{CE}} = 1\text{ V}$	63	100	160	
			100	160	250	
h_{FE}	DC current gain BSX62-10; BSX63-10 BSX62-16; BSX63-16	$I_{\text{C}} = 2\text{ A}; V_{\text{CE}} = 5\text{ V}$	–	70	–	
			–	120	–	
V_{CEsat}	collector-emitter saturation voltage	$I_{\text{C}} = 1\text{ A}; I_{\text{B}} = 100\text{ mA}$	–	–	700	mV
		$I_{\text{C}} = 2\text{ A}; I_{\text{B}} = 200\text{ mA}$	–	–	800	mV
V_{BEsat}	base-emitter saturation voltage	$I_{\text{C}} = 1\text{ A}; I_{\text{B}} = 100\text{ mA}$	–	–	1.2	V
		$I_{\text{C}} = 2\text{ A}; I_{\text{B}} = 200\text{ mA}$	–	–	1.3	V
V_{BE}	base-emitter voltage	$I_{\text{C}} = 100\text{ mA}; V_{\text{CE}} = 1\text{ V}$	–	–	1	V
		$I_{\text{C}} = 1\text{ A}; V_{\text{CE}} = 1\text{ V}$	–	–	1.2	V
		$I_{\text{C}} = 2\text{ A}; V_{\text{CE}} = 5\text{ V}$	–	–	1.3	V
C_{c}	collector capacitance	$I_{\text{E}} = I_{\text{e}} = 0; V_{\text{CB}} = 10\text{ V}; f = 1\text{ MHz}$	–	–	70	pF
f_{T}	transition frequency	$I_{\text{C}} = 200\text{ mA}; V_{\text{CE}} = 10\text{ V}; f = 100\text{ MHz}$	30	70	–	MHz
Switching times (between 10% and 90% levels)						
t_{on}	turn-on time	$I_{\text{Con}} = 1\text{ A}; I_{\text{Bon}} = 50\text{ mA}; I_{\text{Boff}} = -50\text{ mA}$	–	–	300	ns
t_{off}	turn-off time		–	–	1.5	μs

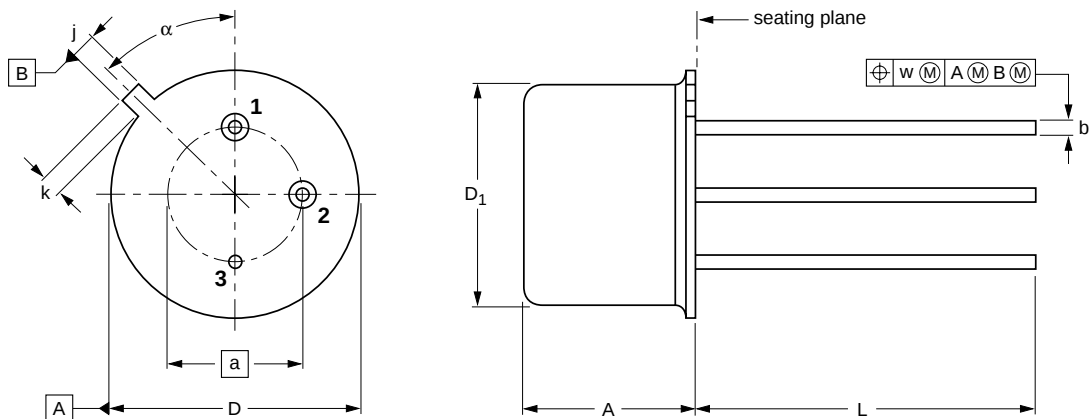
NPN switching transistors

BSX62; BSX63

PACKAGE OUTLINE

Metal-can cylindrical single-ended package; 3 leads

SOT5/11



DIMENSIONS (mm are the original dimensions)

UNIT	A	a	b	D	D ₁	j	k	L	w	α
mm	6.60 6.35	5.08	0.48 0.41	9.39 9.08	8.33 8.18	0.85 0.75	0.95 0.75	14.2 12.7	0.2	45°

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT5/11		TO-39				97-04-11

NPN switching transistors

BSX62; BSX63

DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

LIFE SUPPORT APPLICATIONS

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NPN switching transistors

BSX62; BSX63

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SCA54

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